

Abstract

VAPOR DEPOSITION PROCESSES FOR FORMING SILICON- AND NITROGEN-CONTAINING THIN FILMS

ALD processes for forming the silicon and nitrogen containing films using mono-substituted TSA precursors are disclosed. The mono-substituted TSA precursors have the formula: $(\text{SiH}_3)_2\text{N-SiH}_2\text{-X}$, wherein X is a halogen atom or an amino group.

[FIG 10]